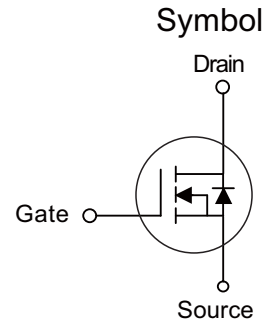


■ PRODUCT CHARACTERISTICS

VDSS	40V
$R_{DS(on)}$ Typ(@ $V_{GS}=4.5$ V)	10m Ω
$R_{DS(on)}$ Typ(@ $V_{GS}=10$ V)	6m Ω
ID	45A



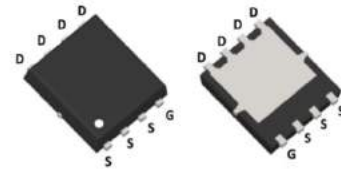
■ APPLICATIONS

- DC/DC Converter

■ FEATURES

- Very low on-resistance $R_{DS(on)}$
- Pb-free lead plating

PDFN5X6-8L



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT4170G	PDFN5X6-8L	5000 pieces /Reel

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	45	A
Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	$I_D(100^{\circ}\text{C})$	31.8	A
Pulsed Drain Current (Package Limited)	I_{DM}	180	A
Maximum Power Dissipation	P_D	28	W
Derating factor		0.22	W/ $^{\circ}\text{C}$
Single pulse avalanche energy	E_{AS}	115	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

■ THERMAL DATA

Parameter	Symbol	Limit	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	4.5	$^{\circ}\text{C}/\text{W}$

■ Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	6	7.2	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	10	12	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=20A$		30	-	S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	831	-	PF
Output Capacitance	C_{oss}		-	318	-	PF
Reverse Transfer Capacitance	C_{rss}		-	24	-	PF
Switching characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=20A$ $V_{GS}=10V, R_G=1.6\Omega$	-	6	-	nS
Turn-on Rise Time	t_r		-	2.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	23	-	nS
Turn-Off Fall Time	t_f		-	3	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=20A,$ $V_{GS}=10V$	-	17.6	-	nC
Gate-Source Charge	Q_{gs}		-	3.5		nC
Gate-Drain Charge	Q_{gd}		-	3.1		nC
Drain-source diode characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$	-		1.2	V
Diode Forward Current	I_S		-	-	45	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = I_S$	-	11	-	nS
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s$	-	19	-	nC

■ TYPICAL CHARACTERISTICS

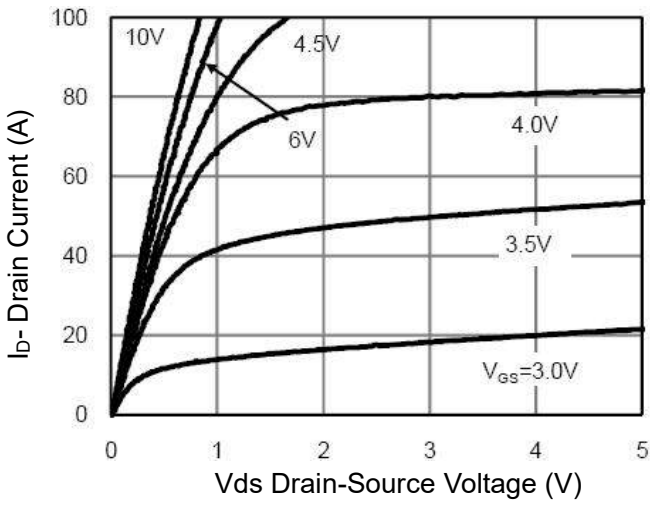


Figure 1 Output Characteristics

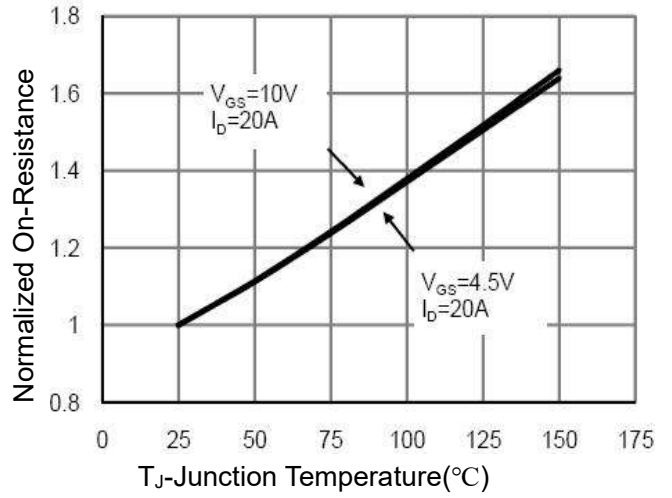


Figure 2 R_{dson} -Junction Temperature

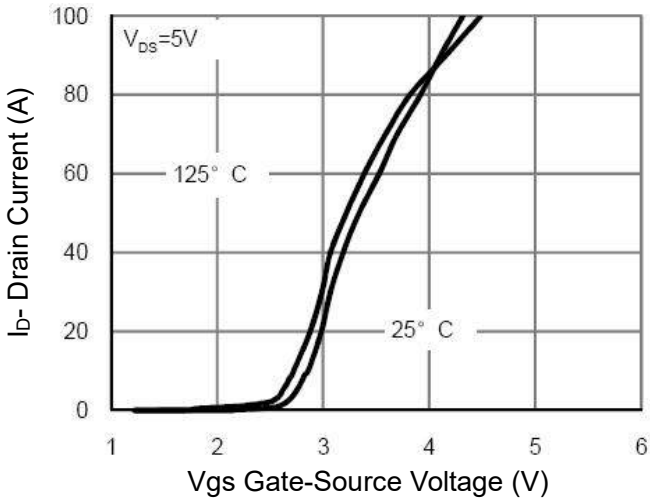


Figure 3 Transfer Characteristics

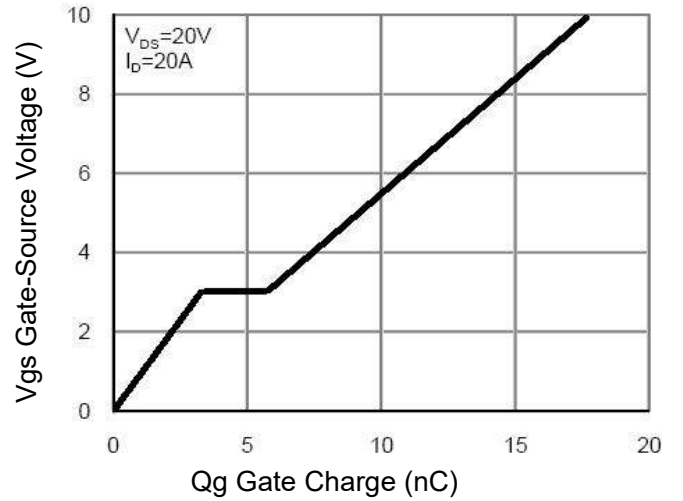


Figure 4 Gate Charge

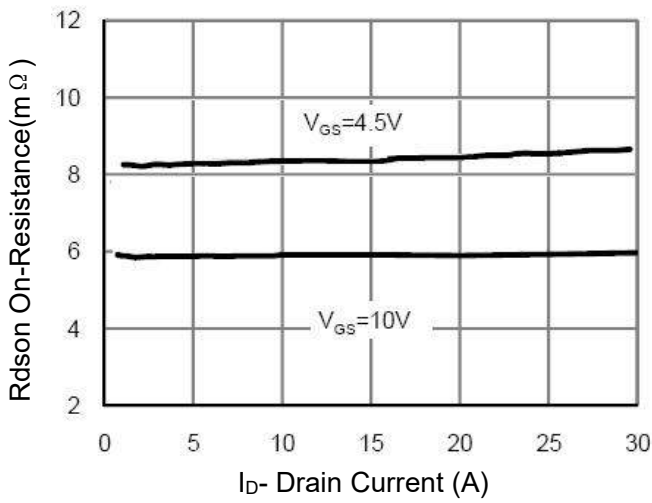


Figure 5 R_{dson} - Drain Current

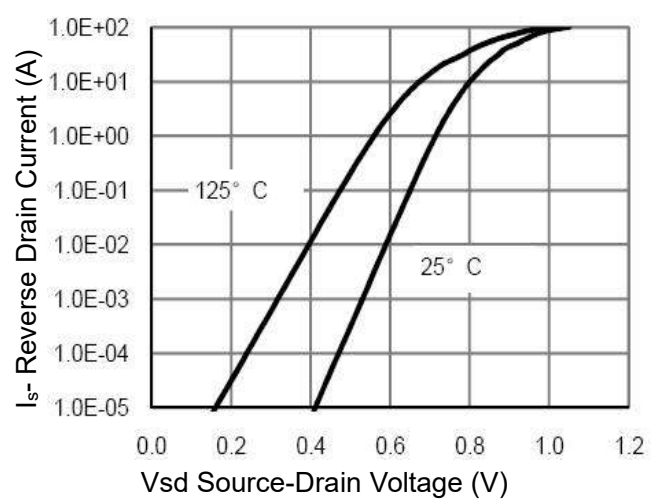


Figure 6 Source- Drain Diode Forward

■ TYPICAL CHARACTERISTICS(Cont.)

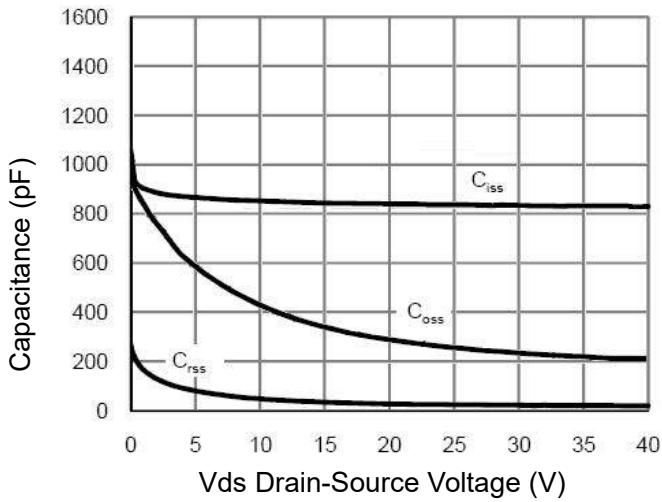


Figure 7 Capacitance vs Vds

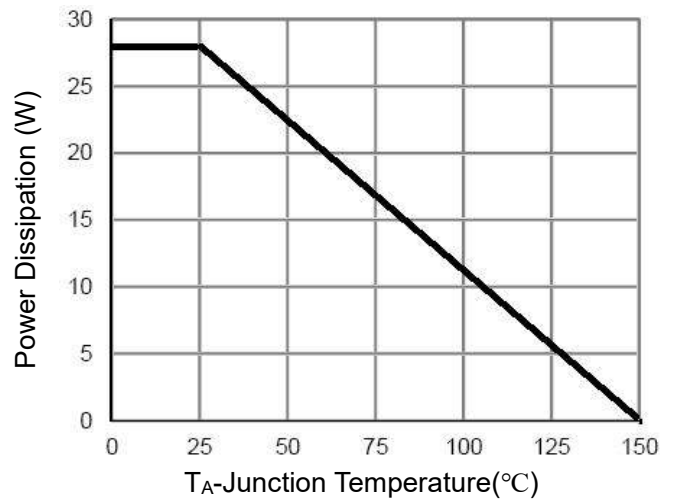


Figure 8 Power De-rating

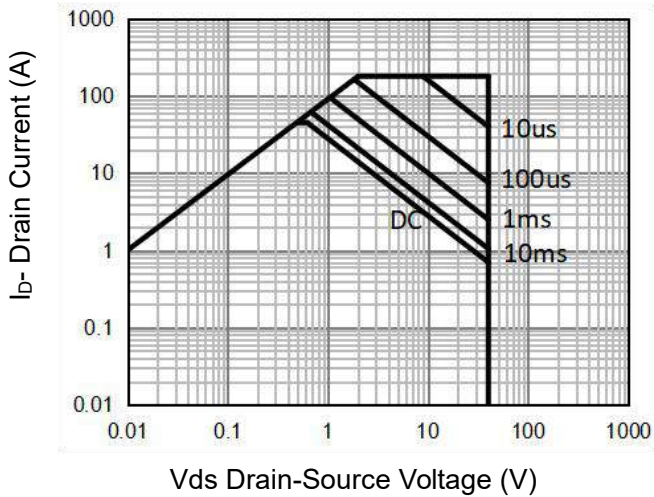


Figure 9 Safe Operation Area (Note 3)

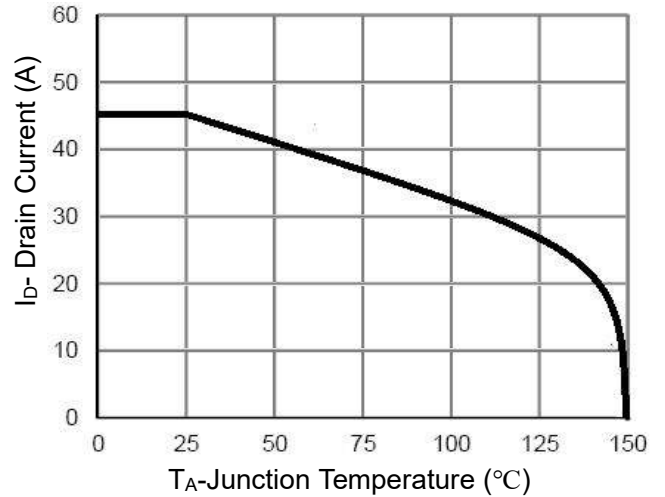


Figure 10 Current De-rating

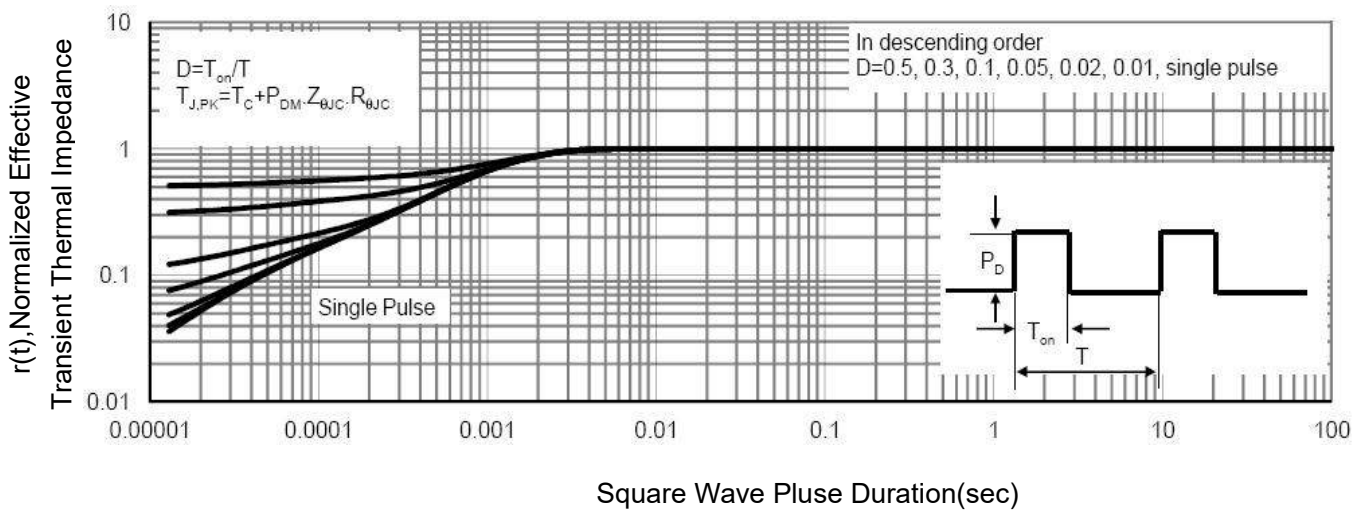
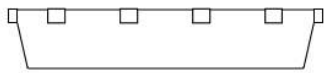
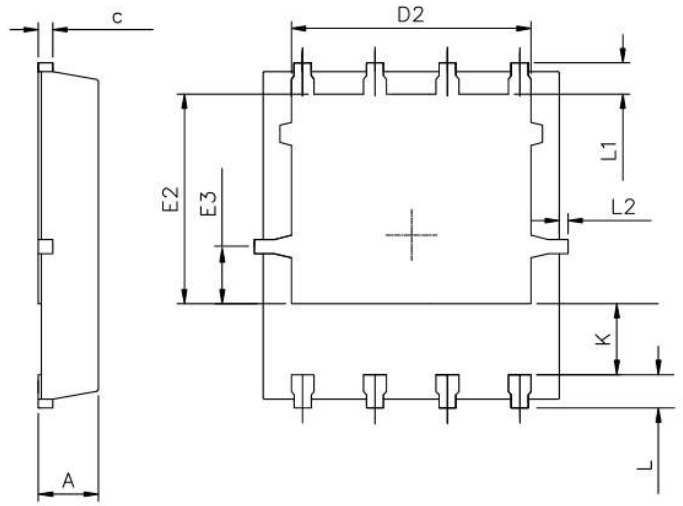
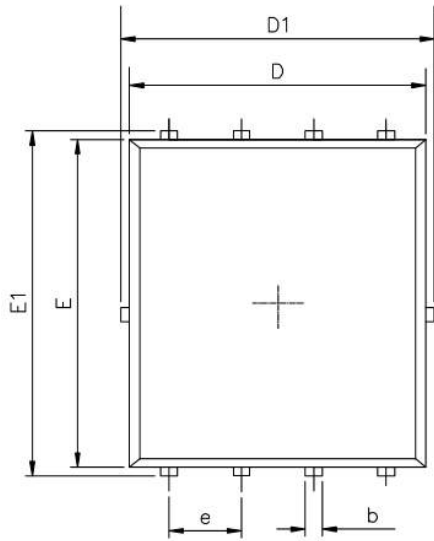
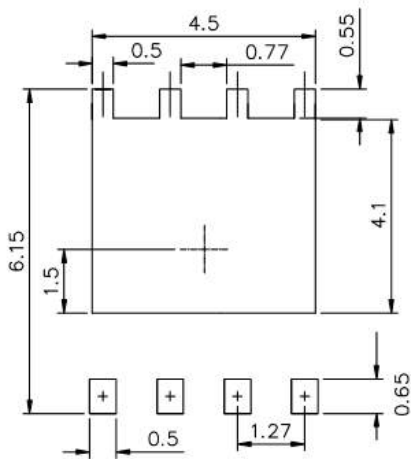


Figure 11 Normalized Maximum Transient Thermal Impedance

■ PDFN5X6-8L Package Mechanical Data



RECOMMENDED LAND PATTERN



UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50